BAS21HT1G, NSVBAS21HT1G, NSVBAS21HT3G

High Voltage Switching Diode

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_{R}	250	Vdc
Repetitive Peak Reverse Voltage	V_{RRM}	250	Vdc
Peak Forward Current	I _F	200	mAdc
Repetitive Peak Forward Current	I _{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current, 60 Hz	I _{FSM(surge)}	625	mAdc
Non-Repetitive Peak Forward Current (Square Wave, $T_J = 25^{\circ}C$ prior to surge) $t = 1 \ \mu s$ $t = 10 \ \mu s$ $t = 100 \ \mu s$ $t = 1 \ ms$ $t = 1 \ s$	I _{FSM}	20 20 10 4 1	Α

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C	P _D	200	mW
Derate above 25°C		1.57	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	635	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	–55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 Minimum Pad

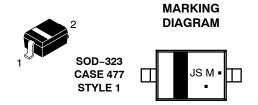


ON Semiconductor®

http://onsemi.com

HIGH VOLTAGE SWITCHING DIODE





JS = Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

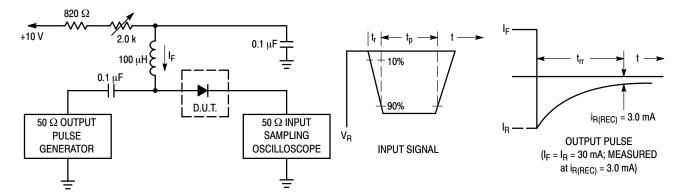
Device	Package	Shipping [†]
BAS21HT1G	SOD-323 (Pb-Free)	3000 / Tape & Reel
NSVBAS21HT1G	SOD-323 (Pb-Free)	3000 / Tape & Reel
NSVBAS21HT3G	SOD-323 (Pb-Free)	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Reverse Voltage Leakage Current $(V_R = 200 \text{ Vdc})$ $(V_R = 200 \text{ Vdc}, T_J = 150^{\circ}\text{C})$	I _R	-	0.1 100	μAdc	
Reverse Breakdown Voltage (I _{BR} = 100 μAdc)	V _(BR)	250	-	Vdc	
Forward Voltage (I _F = 100 mAdc) (I _F = 200 mAdc)	V _F	-	1000 1250	mV	
Diode Capacitance (V _R = 0, f = 1.0 MHz)	C _D	-	5.0	pF	
Reverse Recovery Time $(I_F = I_R = 30 \text{ mAdc}, R_L = 100 \Omega)$	t _{rr}	-	50	ns	



Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 30 mA.

- 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
- 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

BAS21HT1G, NSVBAS21HT1G, NSVBAS21HT3G

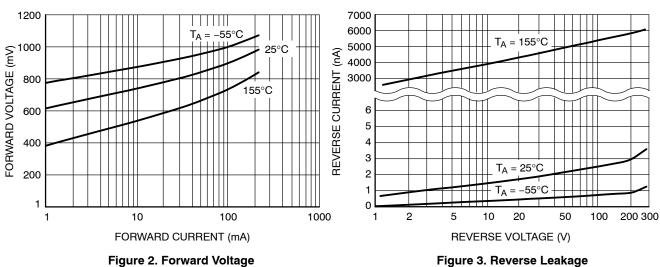


Figure 2. Forward Voltage

1.0

0.9

0.8

0.7

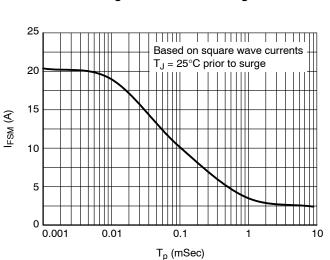
0.6

0.5

0.4

0.3

C_d, DIODE CAPACITANCE (pF)



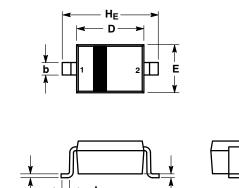
V_R, REVERSE VOLTAGE (V) Figure 4. Diode Capacitance

Figure 5. Maximum Non-repetitive Peak Forward Current as a Function of Pulse **Duration, Typical Values**

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PACKAGE DIMENSIONS

SOD-323 CASE 477-02 ISSUE G



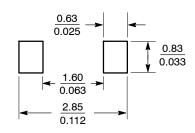
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETERS.
- LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. DIMENSION L IS MEASURED FROM END OF RADIUS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF		0.006 REF			
b	0.25	0.32	0.4	0.010	0.012	0.016
С	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
He	2.30	2.50	2.70	0.090	0.098	0.105

STYLE 1: PIN 1. CATHODE 2. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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